

**1. Material** Substrate GaAlAs (P Type) Removed  
 Epitaxial Layer GaAlAs (N/P Type)

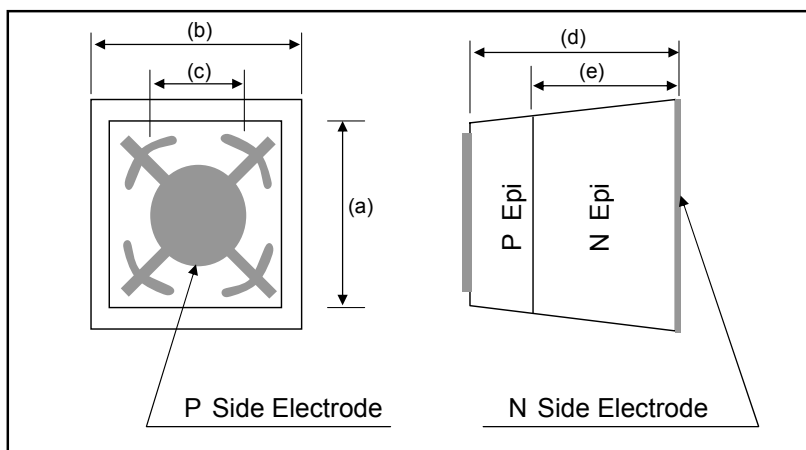
**2. Electrode** N(Cathode) Side Gold Alloy  
 P(Anode) Side Gold Alloy

**3. Electro-Optical Characteristics**

Parameter	Symbol	Min	Typ	Max	Unit	Condition
Forward Voltage	$V_{F(1)}$		1.1		V	IF=10uA
	$V_{F(2)}$		1.6	1.8	V	IF=100mA
Reverse Voltage	$V_R$	5			V	IR=10uA
Power	$P_O$		12.5		mW	IF=50mA
Wavelength	$\lambda_P$		880		nm	IF=50mA
	$\Delta\lambda$		45		nm	IF=50mA
Rise Time	$T_r$		28		ns	
Fall Time	$T_f$		20		ns	

※ Note : Power is measured by Sorter E/T system with bare chip.

**4. Mechanical Data** (a) Emission Area ----- 14.7mil x 14.7mil  
 (b) Bottom Area ----- 15.7mil x 15.7mil  
 (c) Bonding Pad ----- 130um  
 (d) Chip Thickness ----- 4mil  
 (e) Junction Height ----- 4.6mil



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